

April 2011

### FDPF770N15A

# N-Channel PowerTrench<sup>®</sup> MOSFET 150V, 10A, 77m $\Omega$

#### **Features**

- $R_{DS(on)} = 60 m\Omega$  ( Typ.)@  $V_{GS} = 10 V$ ,  $I_D = 10 A$
- · Fast Switching Speed
- Low Gate Charge
- High Performance Trench Technology for Extremely Low  $R_{DS(on)}$
- · High Power and Current Handling Capability
- · RoHS Compliant

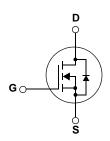
### **Description**

This N-Channel MOSFET is produced using Fairchild Semiconductor's advance PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

### **Application**

- DC to DC Converters
- Synchronous Rectification for Server/Telecom PSU
- Battery Charger
- AC Motor Drives and Uninterruptible Power Supplies
- Off-line UPS





### MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol			Ratings	Units	
$V_{DSS}$	Drain to Source Voltage			150	V
V <sub>GSS</sub>	Gate to Source Voltage			±20	V
1	Drain Current	-Continuous (T <sub>C</sub> = 25°C,Silicon l	_imited)	10	Α
ID	Drain Current	-Continuous (T <sub>C</sub> = 100°C,Silicon	Limited)	7	_ A
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	40	Α
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		35	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		6.0	V/ns	
D	Davier Dissipation	$(T_C = 25^{\circ}C)$		20	W
$P_{D}$	Power Dissipation	- Derate above 25°C		0.16	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C	

### **Thermal Characteristics**

Symbol	Parameter	Ratings	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	5.9	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	

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### **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDPF770N15A	FDPF770N15A	TO-220F	=	=	50

### **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Off Charac	cteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	150	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , Referenced to $25^{\circ}\text{C}$	-	0.1	-	V/°C
1	Zoro Coto Voltago Proin Current	V <sub>DS</sub> = 120V, V <sub>GS</sub> = 0V	-	-	1	
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 120V, T_C = 125^{\circ}C$	-	-	500	μΑ
I <sub>GSS</sub>	Gate to Body Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	±100	nA

#### **On Characteristics**

V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250 \mu A$	2.0	-	4.0	V
R <sub>DS(on)</sub>	Static Drain to Source On Resistance	$V_{GS} = 10V, I_D = 10A$	-	60	77	mΩ
g <sub>FS</sub>	Forward Transconductance	$V_{DS} = 10V, I_D = 10A$ (Note 4)	ı	15	-	S

### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	75/// 01/	-	575	765	pF
C <sub>oss</sub>	Output Capacitance	$V_{DS} = 75V, V_{GS} = 0V$ f = 1MHz		64	85	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 111112	-	3.9	-	pF
C <sub>oss(er)</sub>	Energy Related Output Capacitance	$V_{DS} = 75V, V_{GS} = 0V$		113	-	pF
Q <sub>g(tot)</sub>	Total Gate Charge at 10V		-	8.6	11.2	nC
$Q_{gs}$	Gate to Source Gate Charge	$V_{DS} = 75V, I_{D} = 10A$		3.2	-	nC
Q <sub>gs2</sub>	Gate Charge Threshold to Plateau	V <sub>GS</sub> = 10V	-	1.2	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge	(Note	4.5)	1.9	-	nC
ESR	Equivalent Series Resistance (G-S)	Drain Open,f = 1MHz	-	0.5	-	Ω

### **Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time		-	12	34	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 75V, I_{D} = 10A$	-	8	26	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS} = 10V, R_{GEN} = 4.7\Omega$	-	15	40	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note	1.5) -	3	16	ns

#### **Drain-Source Diode Characteristics**

I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current			-	10	Α
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current			-	40	Α
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS} = 0V, I_{SD} = 10A$	-	-	1.25	V
t <sub>rr</sub>	Reverse Recovery Time	$V_{GS} = 0V, I_{SD} = 10A, V_{DD} = 75V$	-	59	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$ (Note 4)	-	124	-	nC

#### Notes:

- Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. Starting  $T_J=25^{\circ}C,\ L=3mH,\ I_{SD}=4.8A$
- 3. I  $_{SD} \leq$  10A, di/dt  $\leq$  200A/ $\mu$ s,  $V_{DD} \leq$  BV  $_{DSS}$ , Starting T  $_{J}$  = 25°C
- 4. Pulse Test: Pulse width  $\leq 300 \mu s, \ \text{Duty Cycle} \leq 2\%$
- 5. Essentially Independent of Operating Temperature Typical Characteristics

### **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

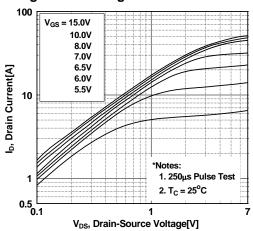


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

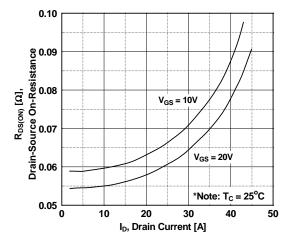


Figure 5. Capacitance Characteristics

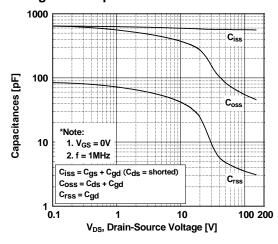


Figure 2. Transfer Characteristics

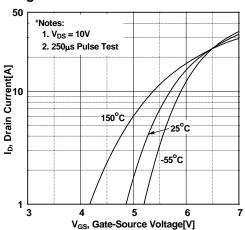


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

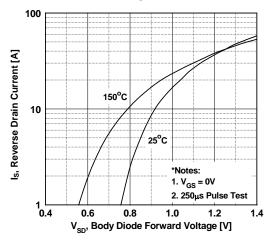
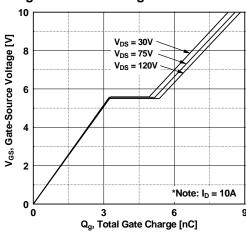


Figure 6. Gate Charge Characteristics



### **Typical Performance Characteristics (Continued)**

Figure 7. Breakdown Voltage Variation vs. Temperature

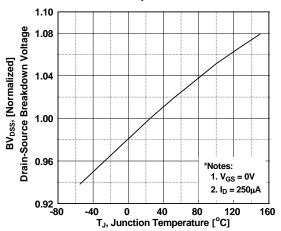


Figure 9. Maximum Safe Operating Area

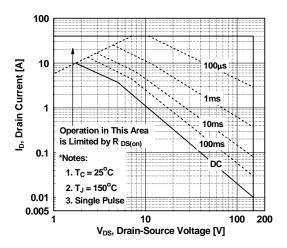


Figure 11. Eoss vs. Drain to Source Voltage

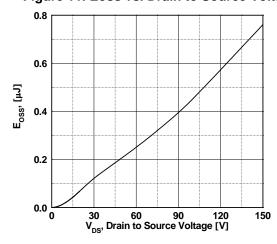


Figure 8. On-Resistance Variation vs. Temperature

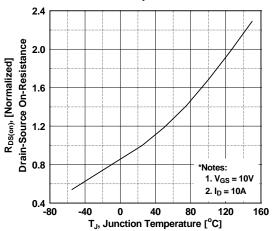
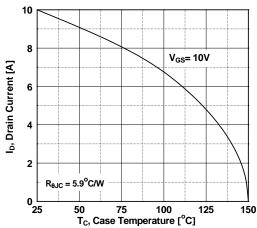


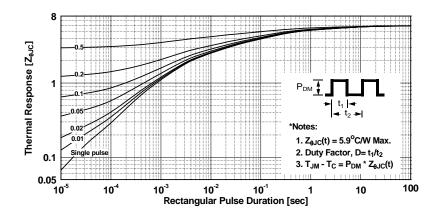
Figure 10. Maximum Drain Current vs. Case Temperature



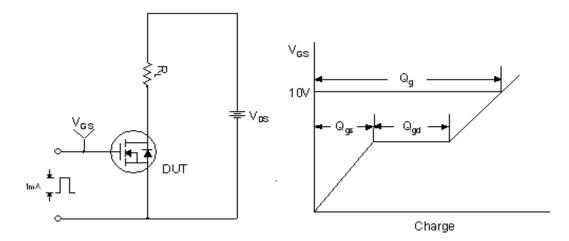
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### **Typical Performance Characteristics** (Continued)

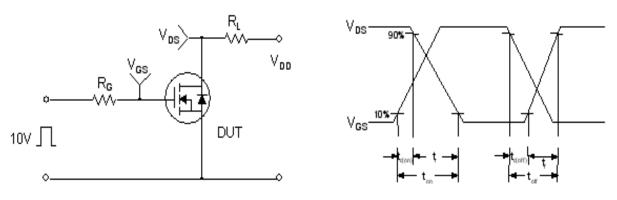
**Figure 12. Transient Thermal Response Curve** 



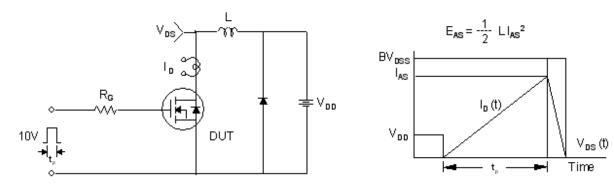
### **Gate Charge Test Circuit & Waveform**



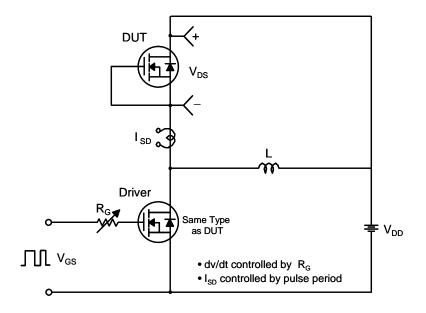
### **Resistive Switching Test Circuit & Waveforms**

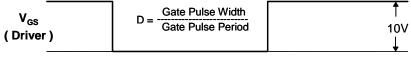


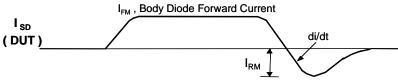
### **Unclamped Inductive Switching Test Circuit & Waveforms**

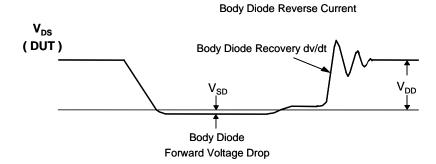


#### Peak Diode Recovery dv/dt Test Circuit & Waveforms



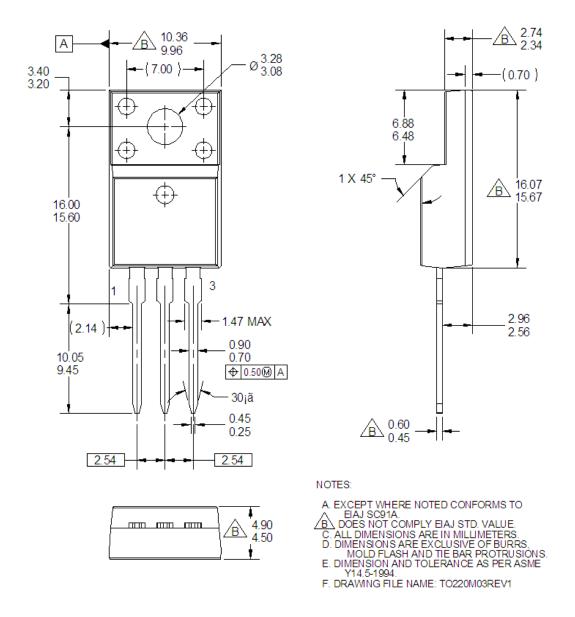






### **Package Dimensions**

## TO-220F (Retractable)



\* Front/Back Side Isolation Voltage : AC 2500V

Dimensions in Millimeters





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